

### T-1 (3mm) INFRA-RED EMITTING DIODES

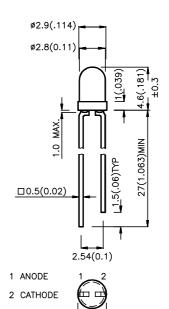
L-934F3C L-934SF4C L-934F3BT L-934SF4BT

#### **Features**

- •MECHANICALLY AND SPECTRALLY MATCHED TO THE L-932P3C PHOTOTRANSISTOR.
- **•BOTH WATER CLEAR LENS AND BLUE TRANSPARENT** LENS AVAILABLE HIGH POWER OUTPUT.

## Description

F3 Made with Gallium Arsenide Infrared Emitting diodes. SF4 Made with Gallium Aluminum Arsenide Emitting diodes.



Package Dimensions

- Notes:
  1. All dimensions are in millimeters (inches).
  2. Tolerance is ±0.25(0.01") unle ssotherwise noted.
  3. Lead spacing is measured where the lead emerance perfection.
- ge package.

  4. Specifications are subjected to change without notice.

ø3.2(0.126)

## Selection Guide

Part No.	Lens Type	lv (mW/sr	Viewing Angle	
		Min.	Max.	201/2
L-934F3C	Water Clear	3.2	20	50°
L-934F3BT	Blue Transparent	3.2	20	50°
L-934SF4C	Water Clear	3.2	20	50°
L-934SF4BT	Blue Transparent	3.2	20	50°

Note: 1.  $\theta$ 1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.

# Electrical / Optical Characteristics at $T_A$ =25°C

Item	P/N	Symbol	Тур.	Max.	Unit	Condition
Forward Voltage	L-934F3C L-934F3BT L-934SF4C L-934SF4BT	VF	1.2 1.2 1.3 1.3	1.5 1.5 1.7 1.7	V	IF=20mA
Reverse Current	L-934F3C L-934F3BT L-934SF4C L-934SF4BT	IR	-	10 10 10 10	uA	VR=5V
Junction Capacitance	L-934F3C L-934F3BT L-934SF4C L-934SF4BT	Со	90 90 90 90	-	pF	V=0 f=1MHz
Peak Spectral Wavelength	L-934F3C L-934F3BT L-934SF4C L-934SF4BT	IR	940 940 880 880	-	nm	IF=20mA
Spectral Bandwidth	L-934F3C L-934F3BT L-934SF4C L-934SF4BT	Δλ	50 50 50 50	-	nm	IF=20mA

# Absolute Maximum Ratings at $T_A$ =25°C

Item	Symbol	Maximum Rating	Units
Power Dissipation	Pd	100	mW
Forward Current	IF	50	mA
Peak Forward Current	lp	1.2	А
Reverse Voltage	VR	5	V
Operating Temperature	Topr	-45~ +80	°C
Storage Temperature	Tstg	-45~ +80	°C

Note: 1.lp Condiction : 1/10 Duty Cycle, 0.1ms Pluse Width.

